

Docket: TSMC 98 - 262CC
S/N: 09/325,951

A 1/2800



To: Commissioner of Patents and Trademarks
Washington, D.C. 20231
From: George O. Saile, Reg. No. 19,572
29 Davis Avenue
Poughkeepsie, N.Y. 12603
Subject:

Serial No.: 09/325,951 Filed: 06/04/99
Inventor: Min-Hsiung Chiang

Title: Method For Forming High Purity Silicon Oxide Field
Oxide Isolation Region

Group Art Unit: 2812 Examiner: Pompey, R. E.
Attorney Docket: TSMC 98 - 262CC

RESPONSE TO PATENT OFFICE ACTION

Dear Sir:

In response to the Final office action dated 05/06/03, please consider
the following remarks:

CERTIFICATE OF MAILING

I hereby certify that this correspondence is being deposited with the
United States Postal Service as first class mail in an envelope addressed to:
Commissioner for Patents, P.O. Box 1450, Alexandria, Virginia 22313-1450, on
July 7, 2003

Signature/Date

7/7/03

Stephen B. Ackerman

Reg. No. 37,761

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